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21	125	(magnet\$6 adj2 junction) and etch\$3	USPAT	2003/07/03 10:30
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Electron Devices Meeting, 2002. IEDM '02. Digest. International , 8-11 Dec. 2002

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2 Barrier formation in lead-based tunnel junctions studied by surface techniques

Emmanuel, A.; Donaldson, G.; Band, W.; Dew-Hughes, D.;

Magnetics, IEEE Transactions on , Volume: 11 Issue: 2 , Mar 1975

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3 Reactive ion etching in the fabrication of niobium tunnel junctions

Reible, S.;

Magnetics, IEEE Transactions on , Volume: 17 Issue: 1 , Jan 1981

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